



Nanophotonics

Masters and Stamps for Nanoimprint Lithography

AMO offers masters fabricated using various micro- and nanolithography techniques in combination with anisotropic etching.

Large Area Periodic Nanostructures

Using our IL technology allows producing large, spatial coherent and periodic gratings with constant pitch. Pattern transfer and further processing can be carried out according to customer requirements to achieve high aspect ratio gratings with vertical sidewalls.

Pattern type	1 D, rectangular, hexagonal
Substrate material	Silicon or fused silica
Substrate thickness	typical 500 μm to 650 μm
Substrate size	2, 4, 6 and 8 inch
Grating pitch	180 nm to 2500 nm
Etch depth	up to 2500 nm
Line width	40 nm to 1500 nm
Active grating	area up to 90% of the substrate size

Some specifications are matter of negotiation. For further details please contact us.

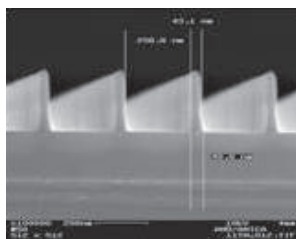
Process Control

All grating dimensions are specified and controlled during and after processing. Line width maps, LER characterisation and defect inspection are available on request.

Arbitrary high resolution Nanostructures

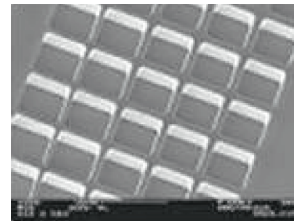
Using our e-Beam lithography (EBL), we can realize arbitrary nanoscale patterns. Our Gaussian beam system provides ultrahigh-resolution down to a few ten nanometers. The definition of large active areas is limited by writing time that is pattern dependent. Pattern transfer into silicon or other material is possible. A quote can easily be provided and is usually based on an electronic design, preferable in GDS format.

Pattern type	arbitrary
Substrate material	Silicon or fused silica
Substrate thickness	typical 500 μm to 650 μm
Substrate size	2, 4, 6 and 8 inch
Smallest feature size	50 nm (or even lower on request)
Etch depth	up to 1000 nm, pattern dependent
Active patterned area	limited by writing time, e.g. a few mm^2 for ultradense patterns



Arbitrary Microstructures

Masters can easily be produced using photolithography. Here micrometer features can be defined and etched up to 10 μm into the substrate. This technique requires a photomask that can either be designed by customer's needs. We have several photomasks on stock that might fit your demands.



Mask Aligner

Pattern type	arbitrary
Substrate material	Silicon or fused silica
Substrate thickness	typical 500 μm to 650 μm
Substrate size	up to 8 inch and any size within
Smallest feature size	2 μm
Etch depth	up to 10 μm
Active patterned area	full substrate

i-line Stepper

Pattern type	Arbitrary field size up to 20x20 mm^2
Substrate material	Silicon or fused silica
Substrate thickness	typical 500 μm to 650 μm
Substrate size	6 inch only
Smallest feature size	0,5 μm
Etch depth	up to 5 μm
Active patterned area	full substrate

Advanced Masters using mixed Technology

Combination of the above mentioned technologies for the fabrication of complex masters available on request.

- Mix-Match between i-line and EBL lithography
- Multi-level-masters, for 3D applications

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